

*Amendment to the Specification*

Please amend paragraph [0001] as follows:

[0001] This application is a continuation of U.S. Ser No. 09/753,664, filed January 4, 2001 (now U.S. Patent No. 6,803,306 that issued October 12, 2004), entitled "High Density Metal Capacitor Using Via Etched Stopping Layer as Field Dielectric in Dual-Damascene Interconnect Process," which is incorporated herein by reference in its entirety.